High Current Transistors

NPN Silicon

Features

• Pb-Free Package is Available*

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
	BC635 BC637 BC639	V _{CEO}	45 60 80	Vdc
	BC635 BC637 BC639	V _{CBO}	45 60 80	Vdc
Emitter-Base Voltage		V_{EBO}	5.0	Vdc
Collector Current – Continuou	ıs	I _C	1.0	Adc
Total Device Dissipation @ T _A Derate above 25°C	Ą = 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T ₀ Derate above 25°C	_C = 25°C	P _D	800 12	mW mW/°C
Operating and Storage Juncti Temperature Range	on	T _J , T _{stg}	–55 to +150	°C

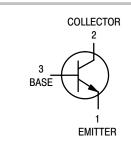
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

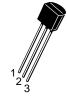
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction–to–Ambient	$R_{ heta JA}$	200	°C/W
Thermal Resistance, Junction–to–Case	$R_{\theta JC}$	83.3	°C/W



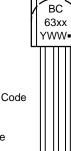
http://onsemi.com



MARKING DIAGRAM



TO-92 CASE 29 STYLE 14



BC63xx = Specific Device Code
Y = Year
WW = Work Week
Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
BC635RL1	TO-92	2000/Tape & Reel
BC635ZL1	TO-92	2000/Ammo Pack
BC637	TO-92	5000 Units/Box
BC639	TO-92	5000 Units/Box
BC639RL1	TO-92	2000/Tape & Reel
BC639ZL1	TO-92	2000/Ammo Pack
BC639-16ZL1	TO-92	2000/Ammo Pack
BC639-16ZL1G	TO-92 (Pb-Free)	2000/Ammo Pack

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•		•	•	•
Collector – Emitter Breakdown Voltage $^{(1)}$ (I _C = 10 μ Adc, I _B = 0)	BC635 BC637 BC639	V _{(BR)CEO}	45 60 80	- - -	- - -	Vdc
Collector – Emitter Zero–Gate Breakdown Volta ($I_C = 100 \mu Adc, I_B = 0$)	age ⁽¹⁾ BC639–16	V _{(BR)CES}	120	-	-	Vdc
Collector – Base Breakdown Voltage ($I_C = 100 \mu Adc, I_E = 0$)	BC635 BC637 BC639	V _(BR) CBO	45 60 80	- - -	- - -	Vdc
Emitter – Base Breakdown Voltage ($I_E = 10 \mu Adc, I_C = 0$)		V _{(BR)EBO}	5.0	_	-	Vdc
Collector Cutoff Current $(V_{CB} = 30 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 30 \text{ Vdc}, I_E = 0, T_A = 125^{\circ}\text{C})$		I _{CBO}	- -	- -	100 10	nAdc μAdc
ON CHARACTERISTICS (Note 1)						
DC Current Gain $(I_C = 5.0 \text{ mAdc}, V_{CE} = 2.0 \text{ Vdc})$ $(I_C = 150 \text{ mAdc}, V_{CE} = 2.0 \text{ Vdc})$ $(I_C = 500 \text{ mA}, V_{CE} = 2.0 \text{ V})$	BC635 BC637 BC639 BC639–16ZLT1	h _{FE}	25 40 40 40 100 25	- - - -	- 250 160 160 250	-
Collector – Emitter Saturation Voltage (I _C = 500 mAdc, I _B = 50 mAdc)		V _{CE(sat)}	-	-	0.5	Vdc
Base – Emitter On Voltage (I _C = 500 mAdc, V _{CE} = 2.0 Vdc)		V _{BE(on)}	-	-	1.0	Vdc
DYNAMIC CHARACTERISTICS				•	•	-
Current - Gain - Bandwidth Product ($I_C = 50 \text{ mAdc}, V_{CE} = 2.0 \text{ Vdc}, f = 100 \text{ MHz}$)		f⊤	-	200	-	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)		C _{ob}	-	7.0	-	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)		C _{ib}	-	50	-	pF

^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle 2.0%.

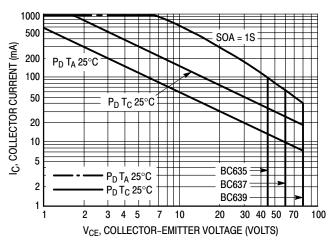


Figure 1. Active Region Safe Operating Area

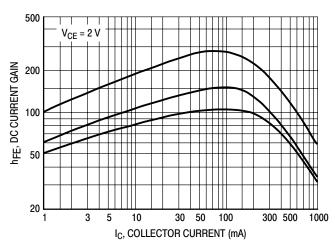


Figure 2. DC Current Gain

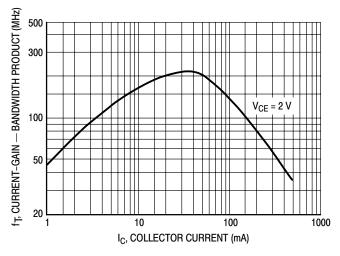


Figure 3. Current-Gain — Bandwidth Product

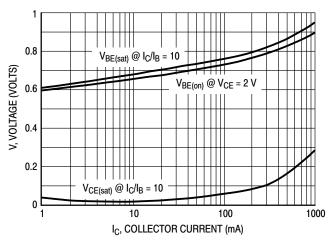


Figure 4. "Saturation" and "On" Voltages

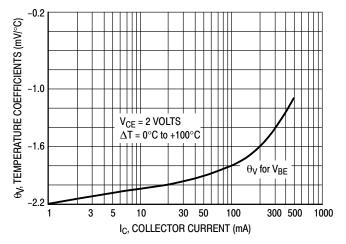
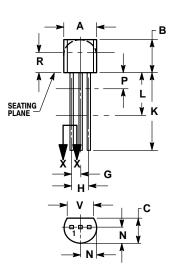
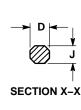


Figure 5. Temperature Coefficients

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AL





NOTES

- DIMENSIONING AND TOLERANCING PER ANSI
 VIA FM 1000
- Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
- 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	MOUTO		MILLIMETERS		
	INCHES		MILLIN	IETEKS	
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.021	0.407	0.533	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
7	0.015	0.020	0.39	0.50	
K	0.500		12.70		
L	0.250		6.35		
N	0.080	0.105	2.04	2.66	
P		0.100		2.54	
R	0.115		2.93		
٧	0 135		3 43		

STYLE 14:

PIN 1. EMITTER 2. COLLECTOR

3. BASE

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